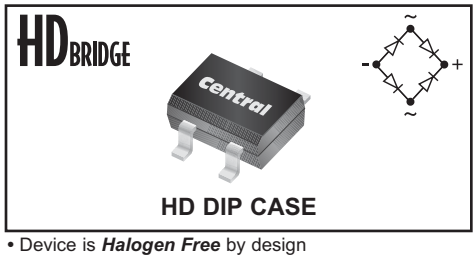
CBRHDSH2-100

SURFACE MOUNT
HIGH DENSITY
2 AMP SILICON
SCHOTTKY BRIDGE RECTIFIER



HD DIP CASE

• Device is ***Halogen Free*** by design

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRHDSH2-100 is a full wave bridge rectifier mounted in a durable epoxy surface mount case, utilizing glass passivated chips.

MARKING CODE: CSH10

FEATURES:

- Low Leakage Current (700nA TYP @ V_{RRM})
- High 2.0A Current Rating
- Low V_F Schottky Diodes (840mV MAX @ I_F=2.0A)

MAXIMUM RATINGS: (T_A=25°C unless otherwise noted)	**SYMBOL**		**UNITS**
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
DC Blocking Voltage	V_R	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	V
Average Forward Current (T_A=75°C)	I_O	2.0	A
Peak Forward Surge Current (8.3ms)	I_{FSM}	50	A
Operating Junction Temperature	T_J	-50 to +125	°C
Storage Temperature	T_{stg}	-50 to +150	°C

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**TYP**	**MAX**	**UNITS**
I_R	V_R=100V	0.70	4.0	μA
V_F	I_F=500mA	610		mV
V_F	I_F=1.0A	700		mV
V_F	I_F=2.0A	770	840	mV
C_J	V_R=4.0V, f=1.0MHz		250	pF

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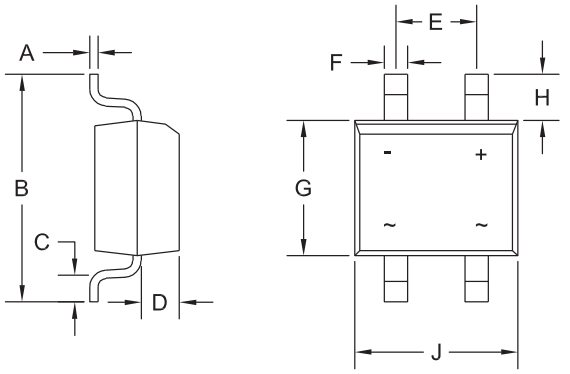
HD DIP CASE - MECHANICAL OUTLINE



R2

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.006	0.014	0.15	0.35
B	-	0.275	-	7.00
C	0.027	0.043	0.70	1.10
D	0.035	0.051	0.90	1.30
E	0.090	0.106	2.30	2.70
F	0.019	0.031	0.50	0.80
G	0.150	0.165	3.80	4.20
H	0.051	0.067	1.30	1.70
J	0.177	0.193	4.50	4.90
K	0.090	0.106	2.30	2.70
L	0.000	0.008	0.00	0.20

HD DIP (REV: R2)

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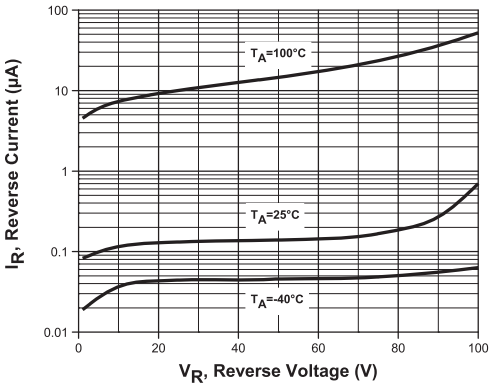
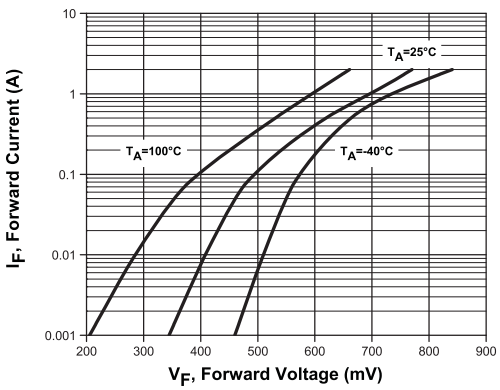
TYPICAL ELECTRICAL CHARACTERISTICS

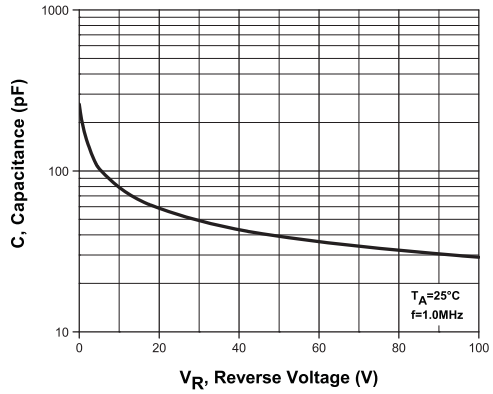
Typical Per Diode Leakage Current



Typical Per Diode Forward Voltage



Typical Per Diode Capacitance



Per Diode Current Derating